

EPITAXIAL-BASE NPN/PNP



BD331 BD332
BD333 BD334
BD335 BD336

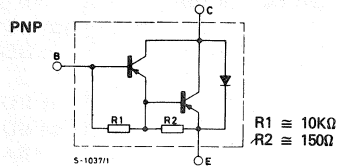
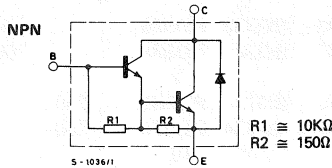
COMPLEMENTARY POWER DARLINGTONS

The BD331, BD333, BD335 (NPN types) and BD332, BD334, BD336 (PNP types) are complementary epitaxial-base Darlingtonts in SOT-82 plastic package. They are intended for use in audio output stages, general amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS		NPN	BD331	BD333	BD335
		PNP	BD332	BD334	BD336
V_{CBO}	Collector-base voltage ($I_E = 0$)		60V	80V	100V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)		60V	80V	100V
V_{EBO}	Base-emitter voltage ($I_C = 0$)			5V	
I_C	Collector current			6A	
I_{CM}	Collector peak current ($t_p < 10$ ms)			10A	
I_B	Base current			0.15A	
P_{tot}	Total power dissipation at $T_{case} \leq 25^\circ C$			60W	
T_{stg}	Storage temperature			-65 to 150°C	
T_j	Junction temperature			150°C	

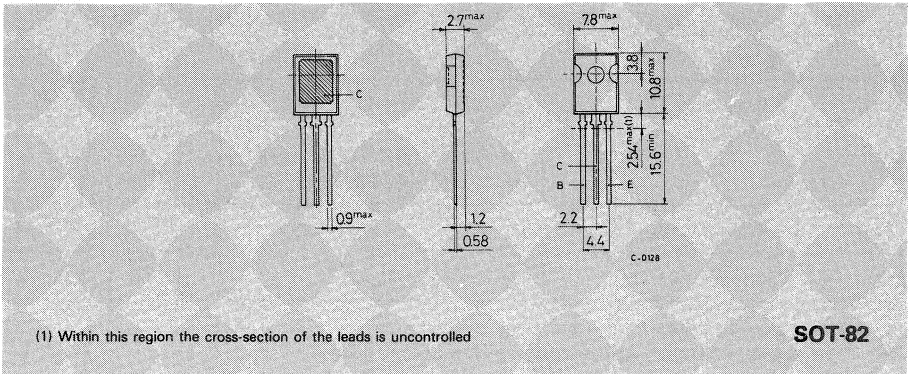
For PNP types voltage and current values are negative

INTERNAL SCHEMATIC DIAGRAMS



MECHANICAL DATA

Dimensions in mm



(1) Within this region the cross-section of the leads is uncontrolled

SOT-82



BD331 BD332
BD333 BD334
BD335 BD336

THERMAL DATA

$R_{th\ j-case}$	Thermal resistance junction-case	max	2.08	°C/W
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

Parameter	Test conditions	Min.	Typ.	Max.	Unit	
I_{CBO}	Collector cutoff current ($I_E = 0$)	$V_{CB} = \text{rated } V_{CBO}$ $T_{case} = 150^{\circ}C$		0.2 2	mA mA	
I_{CEO}	Collector cutoff current ($I_B = 0$)	$V_{CE} = 1/2 V_{CEO\ max}$		0.5	mA	
I_{EBO}	Emitter cutoff current ($I_C = 0$)	$V_{EB} = 5V$		5	mA	
$V_{CE(sat)^*}$	Collector-emitter saturation voltage	$I_C = 3A$	$I_B = 12mA$	2	V	
V_{BE}^*	Base-emitter voltage	$I_C = 3A$	$V_{CE} = 3V$	2.5	V	
h_{FE}^*	DC current gain	$I_C = 0.5A$ $V_{CE} = 3V$ for BD331, BD333, BD335 for BD332, BD334, BD336 $I_C = 3A$ $V_{CE} = 3V$ for BD331, BD333, BD335 for BD332, BD334, BD336 $I_C = 6A$ $V_{CE} = 3V$ for BD331, BD333, BD335 for BD332, BD334, BD336		1900 2700 750 750 3000 400	— — — — — —	
V_F^*	Parallel diode forward voltage	$I_F = 3A$		1.8	V	
h_{fe}	Small signal current gain	$I_C = 3A$ $V_{CE} = 3V$ $f = 1MHz$ for BD331, BD333, BD335 for BD332, BD334, BD336		50 150	— —	
t_{on}	Turn-on time	$I_C = 3A$	$V_{CC} = 30V$	1	2	μs
t_{off}	Turn-off time	$I_{B1} = -I_{B2} = 12mA$		5	10	μs

* Pulsed: pulse duration = 300 μs , duty cycle $\leq 1.5\%$

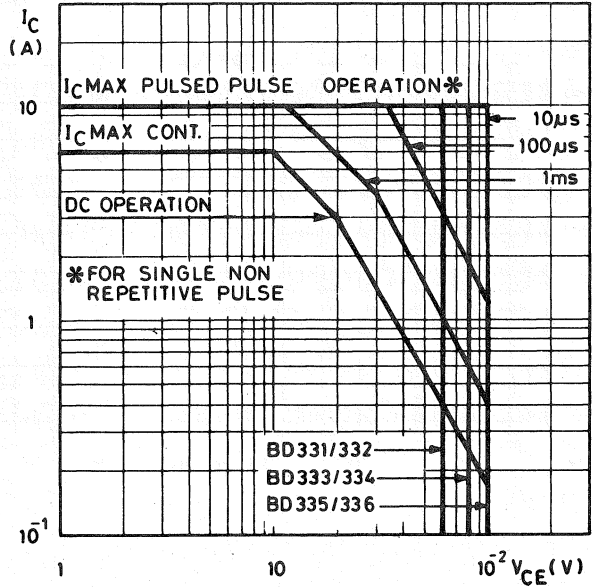
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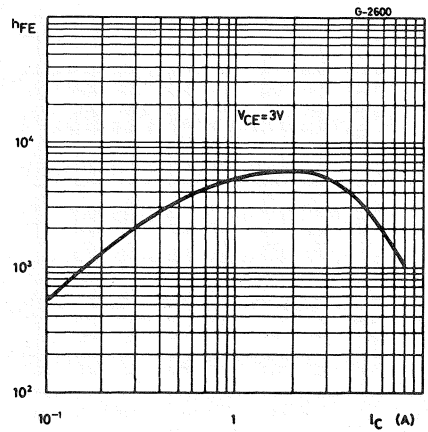
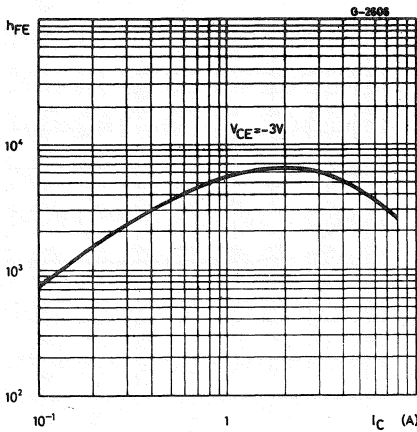
Safe operating areas

G-5359



DC current gain (NPN types)

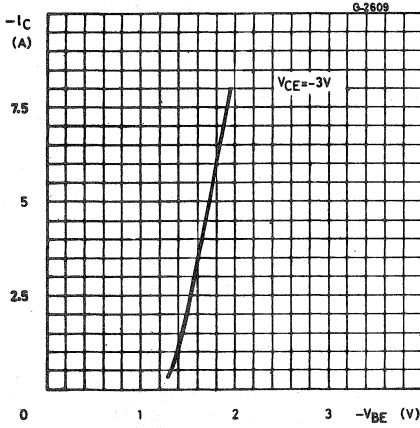
DC current gain (PNP types)



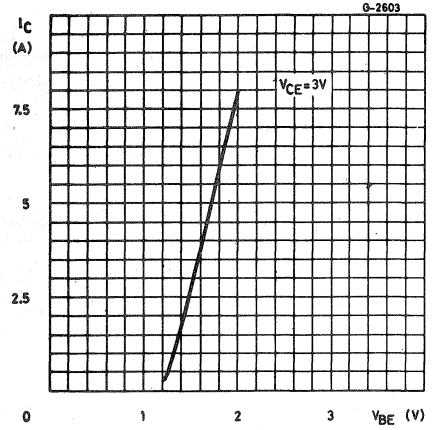


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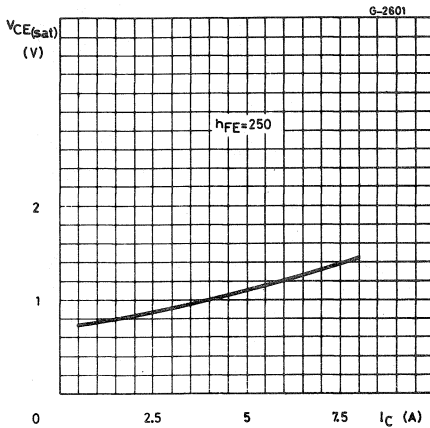
DC transconductance (NPN types)



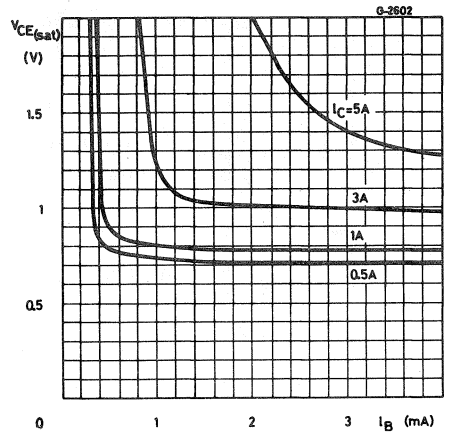
DC transconductance (PNP types)



Collector-emitter saturation voltage (NPN types)



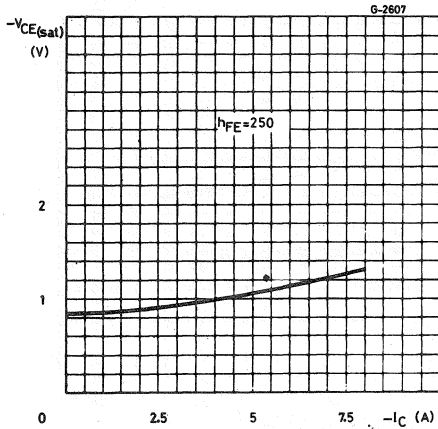
Collector-emitter saturation voltage (PNP types)



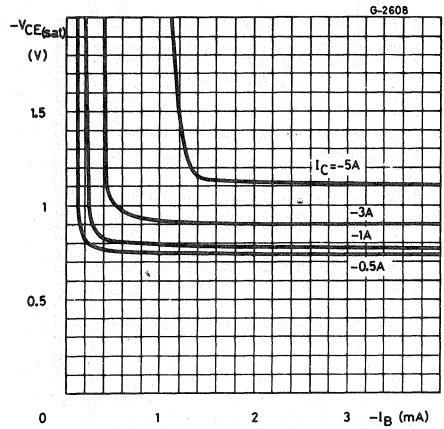


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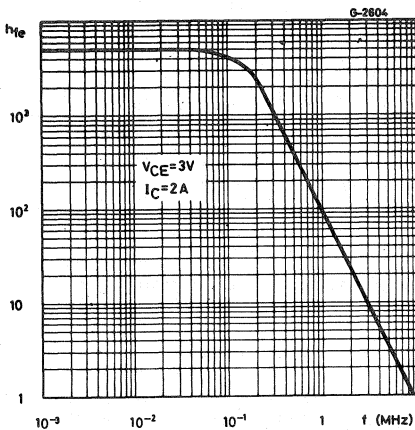
Collector-emitter saturation voltage
(PNP types)



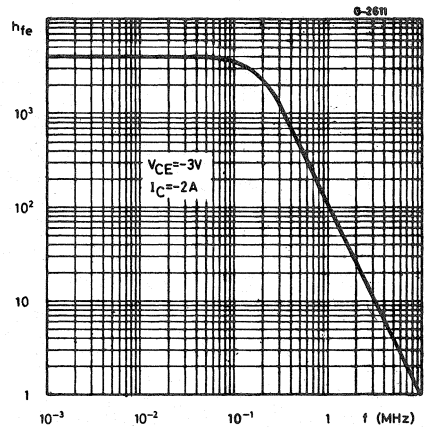
Collector-emitter saturation voltage
(PNP types)



Small signal current gain (NPN types)



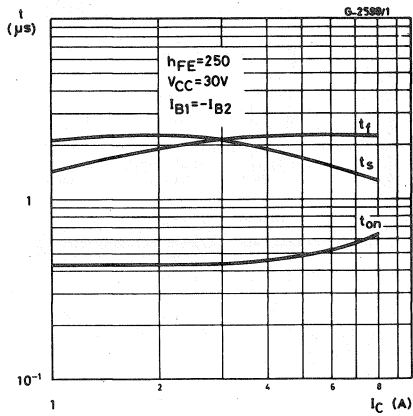
Small signal current gain (PNP types)





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Saturated switching characteristics
(NPN types)



Saturated switching characteristics
(PNP types)

